Type 2N4957UB
Geometry 0006
Polarity PNP
Qual Level: JAN - JANTXV

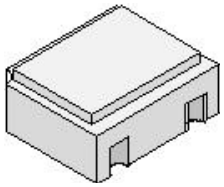
Generic Part Number: 2N4957UB

REF: MIL-PRF-19500/426

Features:

Request Quotation

- Small signal RF silicon transistor designed for high-gain, low-noise applications.
- Housed in a cersot case.
- Also available in chip form using the 0006 chip geometry.
- The Min and Max limits shown are per MIL-PRF-19500/426 which Semicoa meets in all cases.



Cersot

Maximum Ratings

T_C = 25°C unless otherwise specified

Rating	Symbol	Rating	Unit
Collector-Emitter Voltage	V_{CEO}	30	V
Collector-Base Voltage	V_{CBO}	30	V
Emitter-Base Voltage	V_{EBO}	3.0	V
Collector Current, Continuous	I_C	30	A
Operating Junction Temperature	T_J	-65 to +200	°C
Storage Temperature	T_{STG}	-65 to +200	°C

Electrical Characteristics

T_C = 25°C unless otherwise specified

OFF Characteristics	Symbol	Min	Max	Unit
Collector-Base Breakdown Voltage I_C = 100 µA, I_E = 0	$V_{(BR)CBO}$	30	---	V
Collector-Emitter Breakdown Voltage I_C = 1.0 mA, I_B = 0	$V_{(BR)CEO}$	30	---	V
Emitter-Base Breakdown Voltage I_E = 100 µA, I_C = 0	$V_{(BR)EBO}$	3.0	---	V
Collector-Base Cutoff Current V_{CB} = 20 V, I_E 0, T_C = +25°C	I_{CBO1}	---	100	na
Collector-Base Cutoff Current V_{CB} = 20 V, I_E 0, T_C = +150°C	I_{CBO2}	---	100	µA

ON Characteristics	Symbol	Min	Max	Unit
DC Current Gain				
I_C = 0.5 mA, V_{CE} = 10 V	h_{FE1}	15	---	---
I_C = 2.0 mA, V_{CE} = 10 V	h_{FE2}	20	---	---
I_C = 5.0 mA, V_{CE} = 10 V	h_{FE3}	30	165	---
I_C = 5.0 mA, V_{CE} = 10 V, T_A = -55°C	h_{FE4}	10	---	---

Small Signal Characteristics	Symbol	Min	Max	Unit
Magnitude of Common Emitter Small Signal Short Circuit Forward Current Transfer Ratio V_{CE} = 10 V, I_E = 2.0 mA, f = 100 MHz	$\|h_{fe}\|$	12	36	---
Collector to Base Feedback Capacitance V_{CB} = 10 V, I_E = 0, 100 kHz < f < 1 MHz	C_{cb}	---	0.8	pF
Collector to Base Time Constant V_{CB} = 10 V, I_E = 2.0 mA, f = 63.6 MHz	$r_{b'}C_C$	1.0	8.0	ps
Common Emitter Small Signal Power Gain V_{CE} = 10 V, I_C = 2.0 mA, f = 450 MHz	G_{PE}	17	25	dB